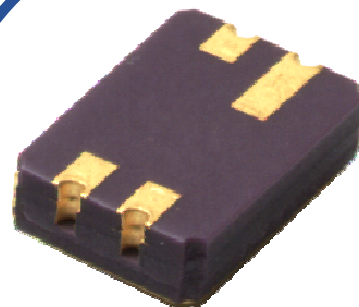


SILICON PLANAR EPITAXIAL PNP TRANSISTOR

2N2907AC3

- Low Power, High Speed Saturated Switching
- Hermetic Surface Mounted Package.
- Ideally suited for High Speed Switching and General Purpose Applications
- Screening Options Available



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage	-60V
V_{CEO}	Collector – Emitter Voltage	-60V
V_{EBO}	Emitter – Base Voltage	-5V
I_C	Continuous Collector Current	-600mA
P_D	Total Power Dissipation at $T_A = 25^\circ\text{C}$ Derate Above 37.5°C	500mW 3.08mW/ $^\circ\text{C}$
T_J	Junction Temperature Range	-65 to $+200^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65 to $+200^\circ\text{C}$

THERMAL PROPERTIES (Each Device)

Symbols	Parameters	Min.	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction To Ambient			325	$^\circ\text{C/W}$

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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Issue 1

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SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2907AC3

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
$V_{(BR)CEO}^{(1)}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}$ $I_B = 0$	-60			V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = -60\text{V}$ $I_E = 0$			-10	μA
		$V_{CB} = -50\text{V}$ $I_E = 0$			-10	nA
		$T_A = 150^\circ\text{C}$			-10	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = -5\text{V}$ $I_C = 0$			-10	μA
		$V_{EB} = -4\text{V}$ $I_C = 0$			-50	nA
I_{CES}	Collector Cut-Off Current	$V_{CE} = -50\text{V}$			-50	nA
$V_{CE(sat)}^{(1)}$	Collector-Emitter Saturation Voltage	$I_C = -150\text{mA}$ $I_B = -15\text{mA}$			-0.4	V
		$I_C = -500\text{mA}$ $I_B = -50\text{mA}$			-1.6	
$V_{BE(sat)}^{(1)}$	Base-Emitter Saturation Voltage	$I_C = -150\text{mA}$ $I_B = -15\text{mA}$	-0.6		-1.3	
		$I_C = -500\text{mA}$ $I_B = -50\text{mA}$			-2.6	
$h_{FE}^{(1)}$	Forward-current transfer ratio	$I_C = -0.1\text{mA}$ $V_{CE} = -10\text{V}$	75			
		$I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}$	100		450	
		$I_C = -10\text{mA}$ $V_{CE} = -10\text{V}$	100			
		$T_A = -55^\circ\text{C}$	50			
		$I_C = -150\text{mA}$ $V_{CE} = -10\text{V}$	100		300	
		$I_C = -500\text{mA}$ $V_{CE} = -10\text{V}$	50			

DYNAMIC CHARACTERISTICS

$ h_{fe} $	Small signal forward-current transfer ratio	$I_C = -20\text{mA}$ $V_{CE} = -20\text{V}$ $f = 100\text{MHz}$	2			
h_{fe}	Small Signal Current Gain	$I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}$ $f = 1.0\text{KHz}$	100			
C_{obo}	Output Capacitance	$V_{CB} = -10\text{V}$ $I_E = 0$ $f = 1.0\text{MHz}$			8	pF
C_{ibo}	Input Capacitance	$V_{EB} = -2\text{V}$ $I_C = 0$ $f = 1.0\text{MHz}$			30	
t_{on}	Turn-On Time	$I_C = -150\text{mA}$ $V_{CC} = -30\text{V}$ $I_{B1} = -15\text{mA}$			45	ns
t_{off}	Turn-Off Time	$I_C = -150\text{mA}$ $V_{CC} = -30\text{V}$ $I_{B1} = -I_{B2} = -15\text{mA}$			300	

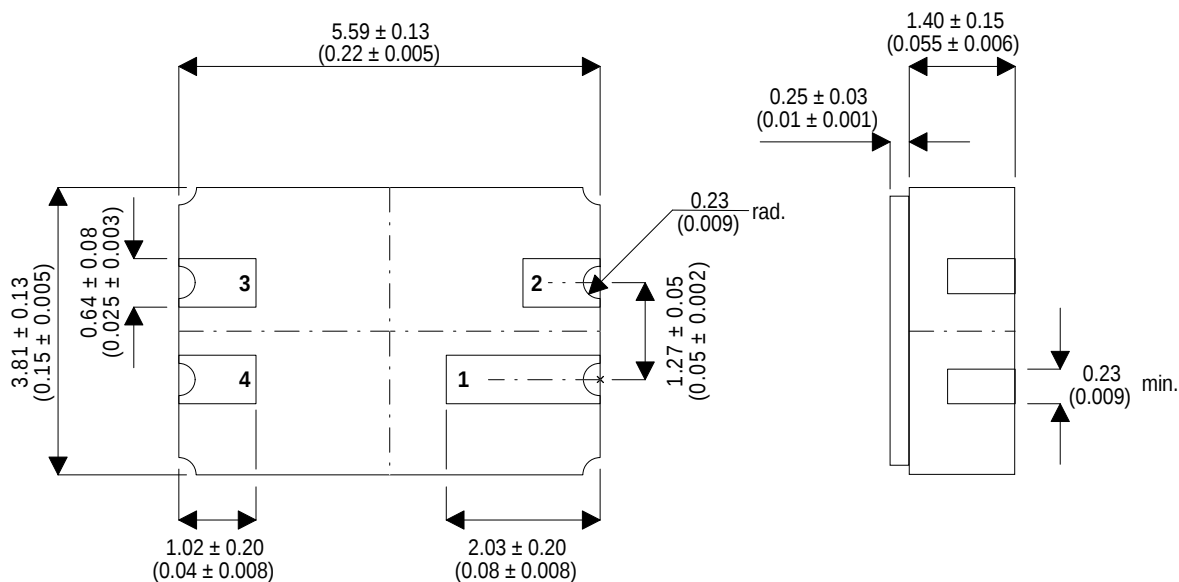
Notes

(1) Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$

SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2907AC3

MECHANICAL DATA

Dimensions in mm (inches)



C3 (MO-041BA)
Underside View

PACKAGE VARIANT TABLE

Variant	Pad 1	Pad 2	Pad 3	Pad 4
A	Collector	N/C	Emitter	Base
B	Collector	N/C	Base	Emitter
C	Collector	Emitter	N/C	Base

N/C = No Connection

SILICON PLANAR EPITAXIAL PNP TRANSISTOR 2N2907AC3

SCREENING OPTIONS

Space Level (JQRS/ESA) and High Reliability options are available in accordance with the [High Reliability and Screening Options Handbook](#) available for download from the from the TT electronics Semelab web site.

ESA Quality Level Products are based on the testing procedures specified in the generic ESCC 5000 and in the corresponding part detail specifications.

Semelabs QR216 and QR217 processing specifications (JQRS), in conjunction with the companies ISO 9001:2000 approval present a viable alternative to the American MIL-PRF-19500 space level processing.

QR217 (Space Level Quality Conformance) is based on the quality conformance inspection requirements of MIL-PRF-19500 groups A (table V), B (table VIa), C (table VII) and also ESA / ESCC 5000 (chart F4) lot validation tests.

QR216 (Space Level Screening) is based on the screening requirements of MIL-PRF-19500 (table IV) and also ESA /ESCC 5000 (chart F3).

JQRS parts are processed to the device data sheet and screened to QR216 with conformance testing to Q217 groups A and B in accordance with MIL-STD-750 methods and procedures.

Additional conformance options are available, for example Pre-Cap Visual Inspection, Buy-Off Visit or Data Packs. These are chargeable and must be specified at the order stage (See Ordering Information). Minimum order quantities may apply.

Alternative or additional customer specific conformance or screening requirements would be considered. Contact Semelab sales with enquiries.

MARKING DETAILS

Parts are typically marked with specification number, serial number (or week of seal) as shown in the example below. .

Customer specific marking requirements can be arranged at time of order but is approximately limited to three lines of 7 Characters. This is to ensure text remains readable.

Example Marking:

SML
2N2907A
001

ORDERING INFORMATION

Part number is built from part, package variant and screening level. The part number can be extended to include the additional options as shown below.

Type – See Electrical Stability Characteristics Table

Package Variant – See Mechanical Data

Screening Level – See Screening Options (ESA / JQRS)

Additional Options:

Customer Pre-Cap Visual Inspection	.CVP
Customer Buy-Off visit	.CVB
Data Pack	.DA
Solderability Samples	.SS
Scanning Electron Microscopy	.SEM
Radiography (X-ray)	.XRAY
Total Dose Radiation Test	.RAD
MIL-PRF-19500 (QR217)	
Group B charge	.GRPB
Group B destructive mechanical samples	.GBDM (12 pieces)
Group C charge	.GRPC
Group C destructive electrical samples	.GCDE (12 pieces)
Group C destructive mechanical samples	.GCDM (6 pieces)
ESA/ESCC	
Lot Validation Testing (subgroup 1) charge	.LVT1
LVT1 destructive samples (environmental)	.L1DE (15 pieces)
LVT1 destructive samples (mechanical)	.L1DM (15 pieces)
Lot Validation Testing (subgroup 2) charge	.LVT2
LVT2 endurance samples (electrical)	.L2D (15 pieces)
Lot Validation Testing (subgroup 3) charge	.LVT3
LVT3 destructive samples (mechanical)	.L3D (5 pieces)

Additional Option Notes:

- 1) All 'Additional Options' are chargeable and must be specified at order stage.
- 2) When Group B,C or LVT is required, additional electrical and mechanical destructive samples must be ordered
- 3) All destructive samples are marked the same as other production parts unless otherwise requested.

Example ordering information:

The following example is for the 2N2907AC3 part, package variant B, JQRS screening, additional Group C conformance testing and a Data pack.

Part Numbers:

2N2907AC3B-JQRS (Include quantity for flight parts)
2N2907AC3B-JQRS.GRPC (chargeable conformance option)
2N2907AC3B-JQRS.GCDE (charge for destructive parts)
2N2907AC3B-JQRS.GCDM (charge for destructive parts)
2N2907AC3B-JQRS.DA (charge for Data pack)

Customers with any specific requirements (e.g. marking, package or screening) may be supplied with a similar alternative part number (there is maximum 20 character limit to part numbers). Contact Semelab sales with all enquiries